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Fujiwara

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(54) **MONOMER, POLYMER, RESIST
COMPOSITION, AND PATTERNING
PROCESS**

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This patent is subject to a terminal dis-
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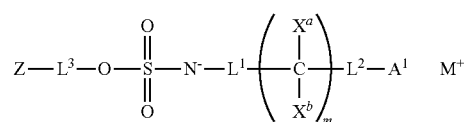
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(57) **ABSTRACT**

A monomer having an onium salt structure represented by
formula (1) gives a polymer which is fully compatible with
resist components. A resist composition comprising the
polymer has advantages including reduced acid diffusion,
high sensitivity, high resolution, a good balance of lithog-
raphy properties, and less defects, and is quite effective for
precise micropatterning.



21 Claims, 1 Drawing Sheet

EXPOSURE

